



IRF7470TRPBF Information



For Reference Only

Part Number IRF7470TRPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 40V 10A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF7470TRPBF Specifications

Manufacturer Part NumberIRF7470TRPBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage8-SOIC (0.154", 3.90mm Width)SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C10A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250µAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 10A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Qate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds Vgs (Max) 12V FET Feature -Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	IRF7470TRPBF
Package 8-SOIC (0.154", 3.90mm Width) Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 10A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.8V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3430pF @ 20V Vgs (Max) ±12V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Infineon Technologies
Package8-SOIC (0.154", 3.90mm Width)SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C10A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 10A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.8V, 10V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3430pF @ 20V Vgs (Max) ±12V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C10A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C10A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	HEXFET?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C10A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.8V, 10V Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature Surplier Device Package Package / Case 10A (Ta) 10A (Ta)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)2.8V, 10VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3430pF @ 20VVgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	10A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	2.8V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max)±12VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	44nC @ 4.5V
FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	3430pF @ 20V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 13 mOhm @ 10A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±12V
Rds On (Max) @ Id, Vgs13 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	13 mOhm @ 10A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

IRF7470TRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF7470TRPBF Payment Methods



















IRF7470TRPBF Shipping Methods













If you have any question about IRF7470TRPBF, please do not hesitate to contact us!

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